

Phase Change Memory Cell and Method of Its Manufacture

ABSTRACT OF THE DISCLOSURE

A phase change memory cell includes a resistive heating element for a phase change body that can expeditiously and efficiently heat a portion of the body with the voltage and current usable with MOSFETs. This is achieved through minimizing the area of an interface between a conductive layer and the body by permitting photolithographic techniques to define one dimension of the interface and thin film deposition techniques to define the other dimension.